

| Subject : Physics<br>Class : XI   |  | Question Paper<br>14: Semicondutor  |   |   |   | - |  |
|-----------------------------------|--|---|---|---|---|---|--|
| i                                 | <ul> <li>Choose to bond and the order is</li></ul> | rgy gap l<br>l valence<br>r of 0.7<br>                                    | <ul> <li><u>N-A</u></li> <li>ect option :</li> <li>between the condu-<br/>band of a substance<br/>eV, then the substance<br/>b) a semiconduct<br/>d) a super conduct<br/>d) a super conduct<br/>f, acceptor impurity<br/>b) indium<br/>d) arsenic<br/>mds formed in p-type<br/>actors are respective<br/>b) 3, 4<br/>d) 5, 4</li> </ul> | e is of<br>ance<br>orc )<br>etor<br>num<br>etor<br>is | Q.5<br>Q.6<br>Q.7<br>Q.8<br>Q.9<br>Q.10 |   | solid crystal.<br>Explain the structure of silicon with the help<br>of proper diagram.<br><u>SECTION C</u><br>Answer the following : (ANY 2) 6<br>Explain the concept of energy band gap.<br>Explain in detail the forward biasing of a p-<br>n junction.<br>What us zero biased p-n junction diode?<br>Draw its diagram.<br><u>SECTION D</u><br>Answer the following : (ANY 1) 4<br>Explain how solids are classified on the basis<br>of band theory of solids.<br><b>Write note on :</b><br>1) Electric devices<br>i) Electronic devices |
| Q.2 :<br>i<br>i<br>Q.3 :<br>Q.4 : | i) Define ex<br>Answer<br>How doe<br>very with     | eV?<br>trinsic se<br><u>SECTIO</u><br>the follor<br>es conduce<br>tempera | miconductor.<br><u>DN B</u><br>wing : (ANY 2)<br>ctivity of semicond  |   |   |   |  |

